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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Daubenspeck *et al.*

Examiner: Sefer, Ahmed

Serial No.: 09/684,463

Art Unit: 2826

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For: **INSULATIVE CAP FOR LASER FUSING**

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Commissioner for Patents
Washington, D.C. 20231

Sir:

This paper is being filed in response to the Office Action mailed October 4, 2002.

Applicants respectfully request that the above-identified patent application be reconsidered in view of the Amendment and Remarks that follow, that the presently pending claims be allowed, and that the application be passed to issue.

In the Specification

The paragraph beginning on page 11, line 3 is as follows based on the amendment herein:

During formation of the device 100, an etch resistant or etch stop layer 130 is deposited on the surface of the [wafer 100] substrate 112, covering the metal wiring layer 114, and particularly, covering the fuse 114A and the alignment mark 142. The etch stop layer 130 is deposited using a spin-on, CVD, PVD or other similar conventionally used deposition technique. The etch stop layer 130 comprises silicon nitride, or other similar material having a slower etch rate than that of the insulative layers thereabove (the reasons for which will be described in more